



BSI Standards Publication

Nanomanufacturing — Key control characteristics

Part 8-1: Nano-enabled metal-oxide interfacial devices — Test method for defect states by thermally stimulated current

National foreword

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**Nanomanufacturing – Key control characteristics –
Part 8-1: Nano-enabled metal-oxide interfacial devices – Test method for defect
states by thermally stimulated current**

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ELECTROTECHNICAL
COMMISSION

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CONTENTS

| | |
|---|----|
| FOREWORD..... | 4 |
| INTRODUCTION..... | 6 |
| 1 Scope..... | 7 |
| 2 Normative references | 7 |
| 3 Terms, definitions, and abbreviated terms | 7 |
| 3.1 Terms and definitions..... | 7 |
| 3.2 Abbreviated terms..... | 8 |
| 4 Measurement of TSC..... | 8 |
| 4.1 General..... | 8 |
| 4.2 Sample preparation..... | 8 |
| 4.3 Experimental procedures | 8 |
| 5 Reporting data..... | 9 |
| 6 Data analysis / interpretation of results..... | 9 |
| 6.1 General..... | 9 |
| 6.2 Peak method [1]..... | 10 |
| 6.3 $T_{\text{start}}-T_{\text{stop}}$ method [2] [3] | 10 |
| 6.4 Initial rise method [4] | 10 |
| Annex A (informative) Case study | 11 |
| A.1 TSC measurement of Au/GaAs (reference sample) | 11 |
| A.1.1 General | 11 |
| A.1.2 Estimating activation energy of defect states by peak method..... | 14 |
| A.2 TSC measurement of Ir/Ta ₂ O ₅ | 18 |
| A.2.1 General | 18 |
| A.2.2 Estimating activation energy of defect states by Peak method | 23 |
| Annex B (informative) Possible methods to analyse TSC spectra..... | 26 |
| B.1 Peak method..... | 26 |
| B.2 $T_{\text{start}}-T_{\text{stop}}$ method | 26 |
| B.3 Initial rise method | 27 |
| Bibliography..... | 29 |
| Figure 1 – Structure of TSC measurement device | 8 |
| Figure 2 – Visualization of TSC measurement sequence..... | 9 |
| Figure A.1 – Photos of (a) the Au electrode configuration on GaAs reference sample, and (b) sample setting | 11 |
| Figure A.2 – Structure of TSC measurement device..... | 12 |
| Figure A.3 – TSC data comparison by samples..... | 13 |
| Figure A.4 – TSC data comparison by heating rate | 14 |
| Figure A.5 – Determination of TSC peak positions using the second derivative curves..... | 16 |
| Figure A.6 – Arrhenius plots of (a) $\ln(T_m^2/\beta)$ vs. $1/T_m$ and (b) $\ln(T_m^4/\beta)$ vs. $1/T_m$ | 17 |
| Figure A.7 – TSC data comparison by samples..... | 19 |
| Figure A.8 – TSC data comparison of Sample A by heating rate | 20 |
| Figure A.9 – TSC data comparison of Sample B by heating rate | 20 |
| Figure A.10 – TSC data comparison of Sample C by heating rate | 21 |

| | |
|--|----|
| Figure A.11 – TSC data comparison by carrier injection method (Samples A, B and C)..... | 22 |
| Figure A.12 – Samples A, B and C: Determination of TSC peak positions using the second derivative curves | 23 |
| Figure A.13 – Arrhenius plots for TA1, Sample A | 24 |
| Figure B.1 – Peak method | 26 |
| Figure B.2 – $T_{\text{start}}-T_{\text{stop}}$ method | 27 |
| Figure B.3 – Determination of trap level energy through initial rise method | 28 |
| Table 1 – TSC measurement sequence steps and parameters | 9 |
| Table A.1 – TSC measurement sequence steps and parameters / case study | 13 |
| Table A.2 – Activation energies of T1 to T6 for $y = \ln (T_m^2/\beta)$ | 17 |
| Table A.3 – Activation energies of T1 to T6 for $y = \ln (T_m^4/\beta)$ | 17 |
| Table A.4 – TSC measurement sequence steps and parameters / case study (2)..... | 18 |
| Table A.5 – Conditions of Ta ₂ O ₅ sputtering deposition..... | 19 |
| Table A.6 – Activation energies of Samples A, B and C | 24 |

INTERNATIONAL ELECTROTECHNICAL COMMISSION

**NANOMANUFACTURING –
KEY CONTROL CHARACTERISTICS –****Part 8-1: Nano-enabled metal-oxide interfacial devices –
Test method for defect states by thermally stimulated current**

FOREWORD

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- the subject is still under technical development or where, for any other reason, there is the future but no immediate possibility of an agreement on an International Standard.

Technical Specifications are subject to review within three years of publication to decide whether they can be transformed into International Standards.

IEC TS 62607-8-1, which is a Technical Specification, has been prepared by IEC technical committee 113: Nanotechnology for electrotechnical products and systems.

The text of this Technical Specification is based on the following documents:

| DTS | Report on voting |
|-------------|------------------|
| 113/493/DTS | 113/510/RVDTS |

Full information on the voting for the approval of this Technical Specification can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 62607 series, published under the general title *Nanomanufacturing – Key control characteristics*, can be found on the IEC website.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

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INTRODUCTION

Thermally stimulated current (TSC) measurement has been a simple and widely used method to get information about charge trapping and electric polarization phenomena of various materials such as dielectrics, ferroelectrics, semiconductors, ceramics, plastics, and other organic materials for the past several decades. Recently, TSC measurement has been recognized as a versatile tool to evaluate defect states and structures in advanced electronic materials including nano-enabled materials and devices. The defect states in devices such as metal-oxide interfacial devices, C-60 FETs, organic LEDs and emerging photovoltaic cells act as charge carrier traps influencing their performance and reliability. As such, a standardized protocol for TSC measurement will be useful to add validity of the experimental data for the purposes of productization of nano-enabled materials and devices. The reference sample for the reproducible TSC measurement is also required.

This document offers a measurement method to be developed for determining defect states of nano-enabled metal-oxide interfacial devices, which is suitable for evaluating the electronic state even though the resistance of the device changes widely.

NANOMANUFACTURING – KEY CONTROL CHARACTERISTICS –

Part 8-1: Nano-enabled metal-oxide interfacial devices – Test method for defect states by thermally stimulated current

1 Scope

There are two types of thermally stimulated current (TSC) measurement methods, classified by the origin of the current. One is generated by the detrapping of charges. The other one is generated by depolarization. This part of IEC 62607 focuses on the former method, and specifies the measurement method to be developed for determining defect states of nano-enabled metal-oxide interfacial devices.

This document includes:

- outlines of the experimental procedures used to measure TSC,
- methods of interpretation of results and discussion of data analysis, and
- case studies.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

ISO/TS 80004-1, *Nanotechnologies – Vocabulary – Part 1: Core terms*

3 Terms, definitions, and abbreviated terms

3.1 Terms and definitions

For the purposes of this document, the terms and definitions given in ISO/TS 80004-1 and the following apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

3.1.1

device under test

DUT

representative sample device used in testing

[SOURCE: IEC 62876-2-1:2018, 3.1.2, modified – In the definition, the word "sample" has been added.]